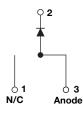
**Vishay Semiconductors** 

### HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 6 A



www.vishay.com



PRODUCT SUMMARY							
Package	TO-263AB (D <sup>2</sup> PAK)						
I <sub>F(AV)</sub>	6 A						
V <sub>R</sub>	1200 V						
V <sub>F</sub> at I <sub>F</sub>	2.4 V						
t <sub>rr</sub> (typ.)	26 ns						
T <sub>J</sub> max.	150 °C						
Diode variation	Single die						

#### FEATURES

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **BENEFITS**

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

#### DESCRIPTION

VS-HFA06TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>BBM</sub>) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V <sub>R</sub>		1200	V					
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	6						
Single pulse forward current	I <sub>FSM</sub>		80	А					
Maximum repetitive forward current	I <sub>FRM</sub>		24						
Maximum power dissinction	D-	T <sub>C</sub> = 25 °C	62.5	W					
Maximum power dissipation	PD	T <sub>C</sub> = 100 °C	25	vv					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					

Revision: 26-Feb-16

Document Number: 94039

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

1







#### Vishay Semiconductors

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J$ = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-				
Maximum forward voltage		I <sub>F</sub> = 6.0 A	-	2.7	3.0	V			
	$V_{FM}$	I <sub>F</sub> = 12 A	-	3.5	3.9				
		I <sub>F</sub> = 6.0 A, T <sub>J</sub> = 125 °C	-	2.4	2.8				
Maximum reverse	I <sub>RM</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	0.26	5.0				
leakage current		$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	110	500	μA			
Junction capacitance	CT	C <sub>T</sub> V <sub>R</sub> = 200 V		9.0	14	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>1</sub> = 25 °C unless of
---

PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
	t <sub>rr</sub>	$I_F = 1.0 \text{ A},  dI_F/dt = 200$	A/μs, V <sub>R</sub> = 30 V	-	26	-				
Reverse recovery time	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	53	80	ns			
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	87	130				
Dock receivery ourrent	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.4	8.0	A nC			
Peak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	$I_F = 6.0 \text{ A}$	-	5.0	9.0				
	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 200 V	-	116	320				
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	233	585				
Peak rate of recovery current during $t_{\rm b}$	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C	]	-	180	-	A // vo			
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	100	-	A/µs			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	2.0				
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W			
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-				
Weight			-	2.0	-	g			
vveigin.			-	0.07	-	oz.			
Marking device		Case style TO-263AB (D <sup>2</sup> PAK)		HFA06	TB120S				



#### **Vishay Semiconductors**

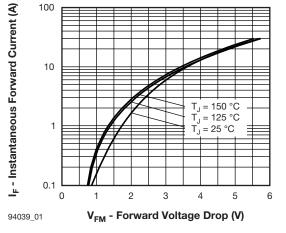


Fig. 1 - Typical Forward Voltage Drop Characteristics

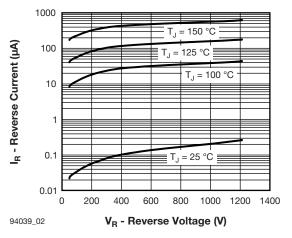


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

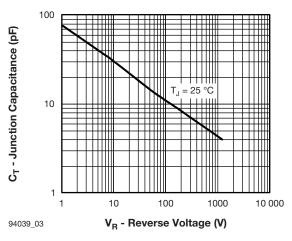


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

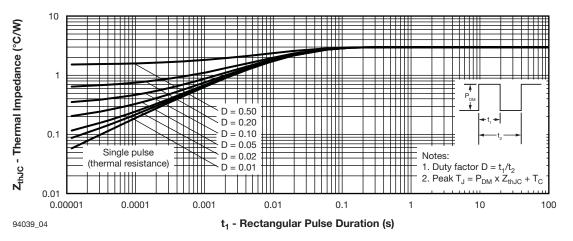


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

 Revision: 26-Feb-16
 3
 Document Number: 94039

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



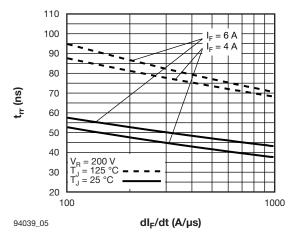


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

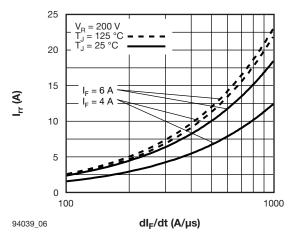


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

## Vishay Semiconductors

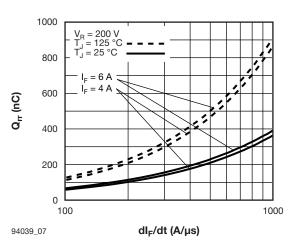


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

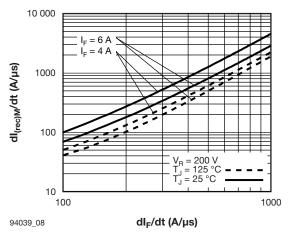


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt

 Revision: 26-Feb-16
 4
 Document Number: 94039

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 DiodesEurope@vishay.com

 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



#### **Vishay Semiconductors**

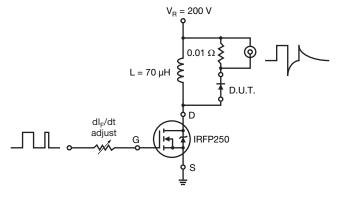


Fig. 9 - Reverse Recovery Parameter Test Circuit

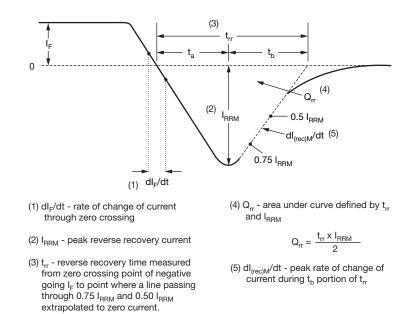


Fig. 10 - Reverse Recovery Waveform and Definitions

#### Vishay Semiconductors

#### **ORDERING INFORMATION TABLE**

Device code	VS-	HF	Α	06	тв	120	S	TRL	PbF			
	1	2	3	4	5	6	7	8	9			
	<ol> <li>Vishay Semiconductors product</li> <li>HEXFRED<sup>®</sup> family</li> </ol>											
	3 -		Process designator: A = electron irradiated									
	4 -	Cur	rent rati	ng (06 =	= 6 A)							
	5 -	Pac	kage ou	utline (TI	B = TO-	220, 2 I	eads)					
	6 -	Volt	tage rati	ng (120	= 1200	V)						
	7 -	S =	D <sup>2</sup> PAK									
	8 -	• N	one = tu	be								
	• TRL = tape and reel (left oriented)											
	<ul> <li>TRR = tape and reel (right oriented)</li> </ul>											
	9 - • PbF = lead (Pb)-free, for tube packaged											
		• P	= lead (	Pb)-free	, for tap	e and r	eel pac	kaged				

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA06TB120SPBF	50	1000	Antistatic plastic tube						
VS-HFA06TB120STRRP	800	800	13" diameter reel						
VS-HFA06TB120STRLP	800	800	13" diameter reel						

VISHAY	
	www.vishay.com

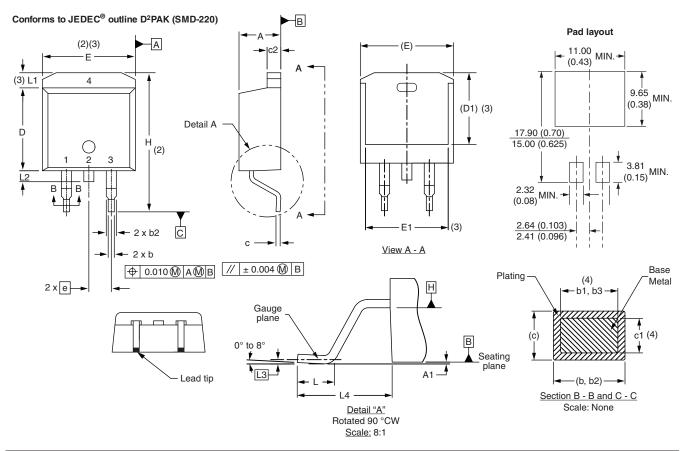
### **Outline Dimensions**



Vishay Semiconductors

D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTED	STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
A	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25 BSC		0.25 BSC 0.010 BSC		
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

Revision: 08-Jul-15

1

Document Number: 95046

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay

### Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.